

Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	Ic	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	833	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

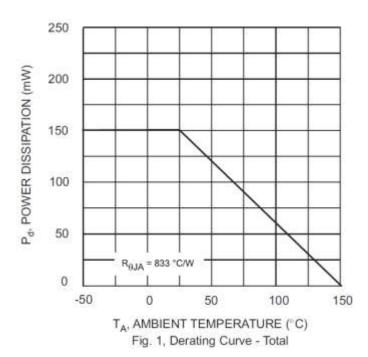
Notes:

^{5.} For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

^{6.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristic and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

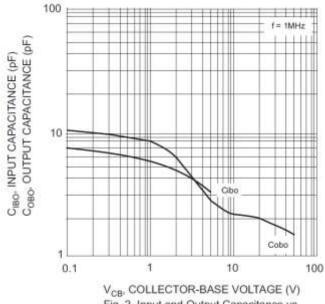
Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-40		V	$I_C = -100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40		V	$I_C = -1 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	-6		V	$I_E = -100\mu A, I_C = 0$	
Collector Cut-Off Current	I _{CEX}	_	-50	nA	VCE = -30V, VEB(OFF) = -3V	
Base Cut-Off Current	I_{BL}	_	-50	nA	VCE = -30V, VEB(OFF) = -3V	
Emitter- Base Cut-Off Current	I _{EBO}	_	-20	nA	$VEB = -6V, I_C = 0$	
ON CHARACTERISTICS (Note 7)						
DC Current Gain	h	60 80 100	— 300		$I_C = -100\mu A$, $V_{CE} = -1V$ $I_C = -1mA$, $V_{CE} = -1V$ $I_C = -10mA$, $V_{CE} = -1V$	
DC Current Gain	h _{FE}	60 30	— —	_	IC = -10MA, VCE = -1V IC = -50MA, V _{CE} = -1V I _C = -100MA, V _{CE} = -1V	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.25 -0.4	V	$I_C = -10$ mA, $I_B = -1$ mA $I_C = -50$ mA, $I_B = -5$ mA	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.65 —	-0.85 -0.95	V	$I_C = -10mA$, $I_B = -1mA$ $I_C = -50mA$, $I_B = -5mA$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	Сово	_	4.5	pF	$V_{CB} = -5V, f = 1MHz, I_{E} = 0$	
Input Capacitance	C _{IBO}	_	10	pF	$V_{EB} = -0.5V$, $f = 1MHz$, $I_C = 0$	
Input Impedance	h _{IE}	2	12	kΩ		
Voltage Feedback Ratio	h _{RE}	0.1	10	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1mA,$	
Small Signal Current Gain	h _{FE}	100	400	_	f = 1kHz	
Output Admittance	hoE	3	60	μS		
Current Gain-Bandwidth Product	f⊤	250	_	MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHz	
Noise Figure	NF	_	4	dB	V_{CE} = -5V, I_C = -100 μ A, R_S = 1k Ω , f = 1kHz	
SWITCHING CHARACTERISTICS						
Delay Time	t _D	_	35	ns		
Rise Time	t _R		35	ns	$V_{CC} = -3V$, $I_{C} = -10mA$,	
Storage Time	ts	_	200	ns	$-I_{B1} = I_{B2} = -1.0 \text{mA}$	
Fall Time	t _F	_	50	ns		

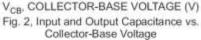
Note:

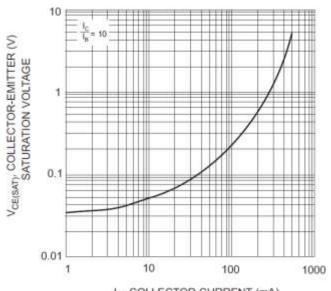
7. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



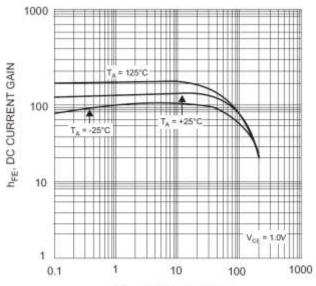
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



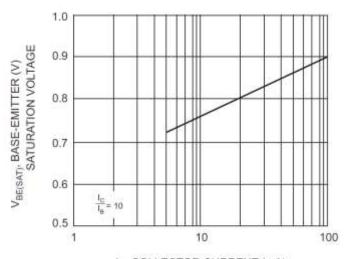




I_C, COLLECTOR CURRENT (mA) Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



I_C, COLLECTOR CURRENT (mA) Fig. 3, Typical DC Current Gain vs Collector Current

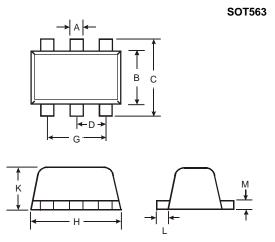


I_C, COLLECTOR CURRENT (mA) Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

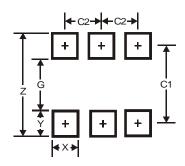


	00	TEAA			
SOT563					
Dim	Min	Max	Тур		
Α	0.15	0.30	0.20		
В	1.10	1.25	1.20		
С	1.55	1.70	1.60		
D	-	-	0.50		
G	0.90	1.10	1.00		
Н	1.50	1.70	1.60		
K	0.55	0.60	0.60		
L	0.10	0.30	0.20		
М	0.10	0.18	0.11		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	SOT563
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5



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